

12. (Original) The Fin structure of Claim 11 wherein said at least one vertically oriented semiconductor body is comprised of single crystalline Si or SiGe.
13. (Original) The Fin structure of Claim 11 wherein said at least one vertically oriented semiconductor body has a hard mask present atop a horizontal surface.
14. (Original) The Fin structure of Claim 11 wherein said at least one vertically oriented semiconductor body has a patterned masking layer thereon, said patterned masking layer not covering said contacts.
15. (Original) The Fin structure of Claim 14 wherein said patterned masking layer is comprised of a conductive material.
16. (Original) The Fin structure of Claim 15 wherein said patterned masking layer is comprised of a non-conductive material.
17. (Original) The Fin structure of Claim 11 wherein said resistor is replaced with a diode.
18. (Original) The Fin structure of Claim 17 wherein said diode includes said contacts that are of opposite dopant style.

19. (Original) The Fin structure of Claim 17 where said diode includes said contacts wherein one of the contacts comprises a doped region having a conductivity type dopant which is different from said dopant region and the other contact is a silicide.